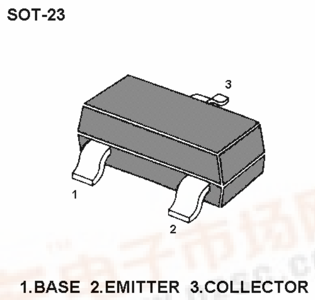
MMBTSA1037

PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into three groups Q, R and S according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Current	$-I_C$	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	-55 to +150	°C

Dated : 20/10/2005

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE}$=6V, $-I_C$=1mA	Q	h_{FE}	120	270	-
	R	h_{FE}	180	390	-
	S	h_{FE}	270	560	-
Collector Cutoff Current at $-V_{CB}$=60V		$-I_{CBO}$	-	0.1	µA
Emitter Cutoff Current at $-V_{EB}$=6V		$-I_{EBO}$	-	0.1	µA
Collector Saturation Voltage at $-I_C$=50mA, $-I_B$=5mA		$-V_{CE(sat)}$	-	0.5	V
Collector Base Breakdown Voltage at $-I_C$=50µA		$-V_{(BR)CBO}$	60	-	V
Collector Emitter Breakdown Voltage at $-I_C$=1mA		$-V_{(BR)CEO}$	50	-	V
Emitter Base Breakdown Voltage at $-I_E$=50µA		$-V_{(BR)EBO}$	6	-	V
Transition Frequency at $-V_{CE}$=12V, $-I_C$=2mA, f=30MHz		f_T	120	-	MHz